

# NTTFS4C10N

## MOSFET – Power, Single, N-Channel, $\mu$ 8FL 30 V, 44 A

### Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- DC-DC Converters
- Power Load Switch
- Notebook Battery Management

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	30	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current $R_{\theta JA}$ (Note 1)	$I_D$	$T_A = 25^\circ\text{C}$	13.3
		$T_A = 80^\circ\text{C}$	9.9
Power Dissipation $R_{\theta JA}$ (Note 1)	$P_D$	$T_A = 25^\circ\text{C}$	2.09
		$T_A = 80^\circ\text{C}$	13.6
Continuous Drain Current $R_{\theta JA} \leq 10$ s (Note 1)	$I_D$	$T_A = 25^\circ\text{C}$	18.2
		$T_A = 80^\circ\text{C}$	13.6
Power Dissipation $R_{\theta JA} \leq 10$ s (Note 1)	$P_D$	$T_A = 25^\circ\text{C}$	3.9
		$T_A = 80^\circ\text{C}$	6.1
Continuous Drain Current $R_{\theta JA}$ (Note 2)	$I_D$	$T_A = 25^\circ\text{C}$	8.2
		$T_A = 80^\circ\text{C}$	6.1
Power Dissipation $R_{\theta JA}$ (Note 2)	$P_D$	$T_A = 25^\circ\text{C}$	0.79
		$T_A = 80^\circ\text{C}$	33
Continuous Drain Current $R_{\theta JC}$ (Note 1)	$I_D$	$T_C = 25^\circ\text{C}$	44
		$T_C = 80^\circ\text{C}$	33
Power Dissipation $R_{\theta JC}$ (Note 1)	$P_D$	$T_C = 25^\circ\text{C}$	23.6
		$T_C = 80^\circ\text{C}$	33
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	$I_{DM}$	128
Operating Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode)	$I_S$	20	A
Drain to Source dV/dt	dV/dt	6.0	V/ns
Single Pulse Drain-to-Source Avalanche Energy ( $T_J = 25^\circ\text{C}, V_{DD} = 50$ V, $V_{GS} = 10$ V, $I_L = 25$ A <sub>pk</sub> , $L = 0.1$ mH, $R_G = 25 \Omega$ ) (Note 3)	$E_{AS}$	31	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.

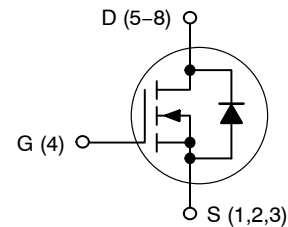


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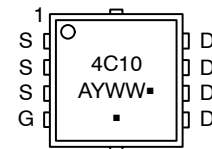
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$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
30 V	7.4 m $\Omega$ @ 10 V	44 A
	11 m $\Omega$ @ 4.5 V	

### N-Channel MOSFET



### MARKING DIAGRAM



4C10 = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NTTFS4C10NTAG	WDFN8 (Pb-Free)	1500 / Tape & Reel
NTTFS4C10NTWG	WDFN8 (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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- Surface-mounted on FR4 board using the minimum recommended pad size.
- This is the absolute maximum ratings. Parts are 100% tested at  $T_J = 25^\circ\text{C}$ ,  $V_{GS} = 10\text{ V}$ ,  $I_L = 17\text{ A}$ ,  $E_{AS} = 14\text{ mJ}$ .

## THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	5.3	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	59.9	
Junction-to-Ambient – Steady State (Note 5)	$R_{\theta JA}$	157.8	
Junction-to-Ambient – ( $t \leq 10\text{ s}$ ) (Note 4)	$R_{\theta JA}$	31.8	

- Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
- Surface-mounted on FR4 board using the minimum recommended pad size.

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\ \mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage (transient)	$V_{(BR)DSS(t)}$	$V_{GS} = 0\text{ V}$ , $I_{D(aval)} = 7.1\text{ A}$ , $T_{case} = 25^\circ\text{C}$ , $t_{transient} = 100\text{ ns}$	34			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			14.5		$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	$\mu\text{A}$
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA

### ON CHARACTERISTICS (Note 6)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$ , $I_D = 250\ \mu\text{A}$	1.3		2.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			4.5		$\text{mV}/^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 30\text{ A}$	5.9	7.4	$\text{m}\Omega$
		$V_{GS} = 4.5\text{ V}$	$I_D = 15\text{ A}$	8.8	11	
Forward Transconductance	$g_{FS}$	$V_{DS} = 1.5\text{ V}$ , $I_D = 15\text{ A}$		43		S
Gate Resistance	$R_G$	$T_A = 25^\circ\text{C}$		1.0		$\Omega$

### CHARGES AND CAPACITANCES

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$ , $V_{DS} = 15\text{ V}$		993		$\text{pF}$
Output Capacitance	$C_{OSS}$			574		
Reverse Transfer Capacitance	$C_{RSS}$			163		
Capacitance Ratio	$C_{RSS}/C_{ISS}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 15\text{ V}$ , $f = 1\text{ MHz}$		0.164		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}$ , $V_{DS} = 15\text{ V}$ ; $I_D = 30\text{ A}$		9.7		$\text{nC}$
Threshold Gate Charge	$Q_{G(TH)}$			1.5		
Gate-to-Source Charge	$Q_{GS}$			2.8		
Gate-to-Drain Charge	$Q_{GD}$			4.8		
Gate Plateau Voltage	$V_{GP}$			3.2		
Total Gate Charge	$Q_{G(TOT)}$		$V_{GS} = 10\text{ V}$ , $V_{DS} = 15\text{ V}$ ; $I_D = 30\text{ A}$		18.6	

### SWITCHING CHARACTERISTICS (Note 7)

- Pulse Test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Switching characteristics are independent of operating junction temperatures.

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## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit	
<b>SWITCHING CHARACTERISTICS</b> (Note 7)							
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 15\text{ A}, R_G = 3.0\ \Omega$		9.0		ns	
Rise Time	$t_r$			30			
Turn-Off Delay Time	$t_{d(OFF)}$			14			
Fall Time	$t_f$			7.0			
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 15\text{ A}, R_G = 3.0\ \Omega$		6.0		ns	
Rise Time	$t_r$			25			
Turn-Off Delay Time	$t_{d(OFF)}$			18			
Fall Time	$t_f$			4.0			
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>							
Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V},$ $I_S = 10\text{ A}$	$T_J = 25^\circ\text{C}$		0.80	1.1	V
			$T_J = 125^\circ\text{C}$		0.67		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 30\text{ A}$		23.3		ns	
Charge Time	$t_a$			12.7			
Discharge Time	$t_b$			10.6			
Reverse Recovery Charge	$Q_{RR}$			8.3			nC

6. Pulse Test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

7. Switching characteristics are independent of operating junction temperatures.

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## TYPICAL CHARACTERISTICS

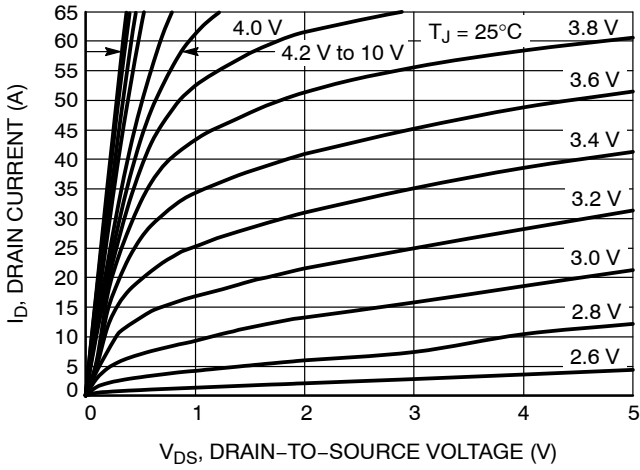


Figure 1. On-Region Characteristics

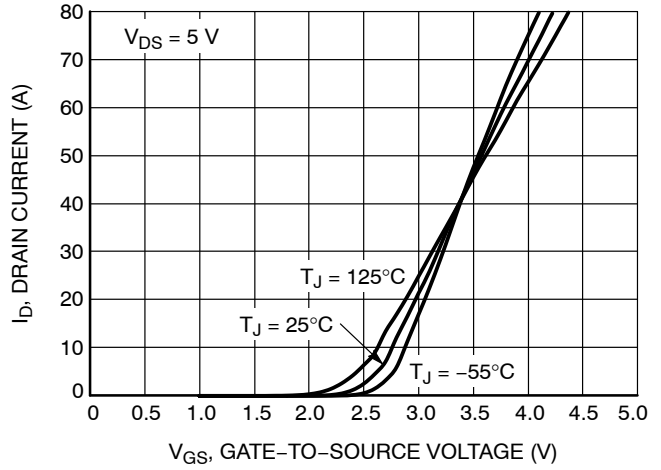


Figure 2. Transfer Characteristics

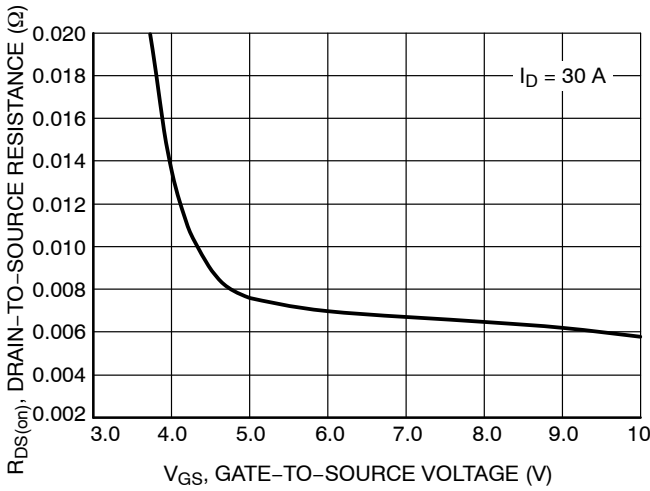


Figure 3. On-Resistance vs.  $V_{GS}$

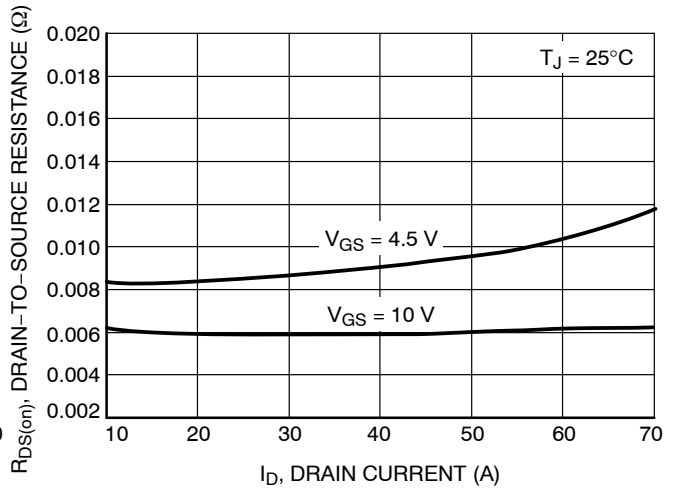


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

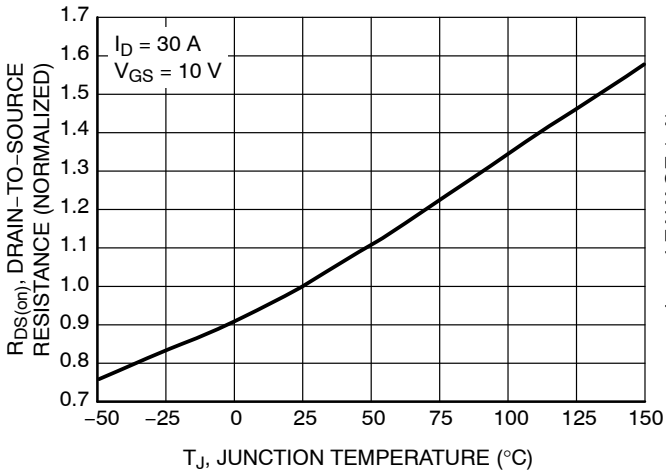


Figure 5. On-Resistance Variation with Temperature

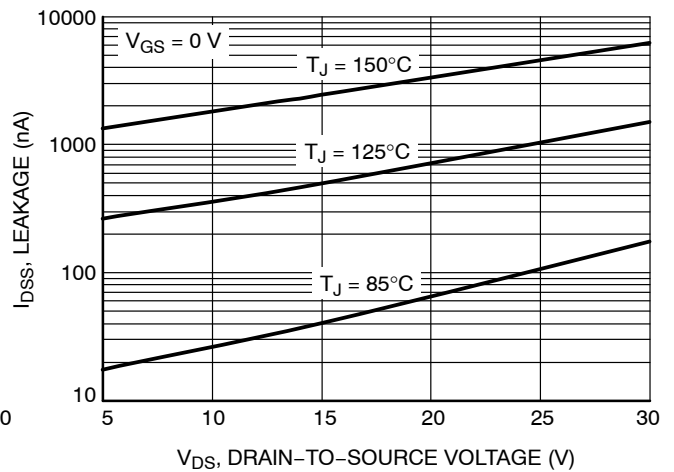


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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## TYPICAL CHARACTERISTICS

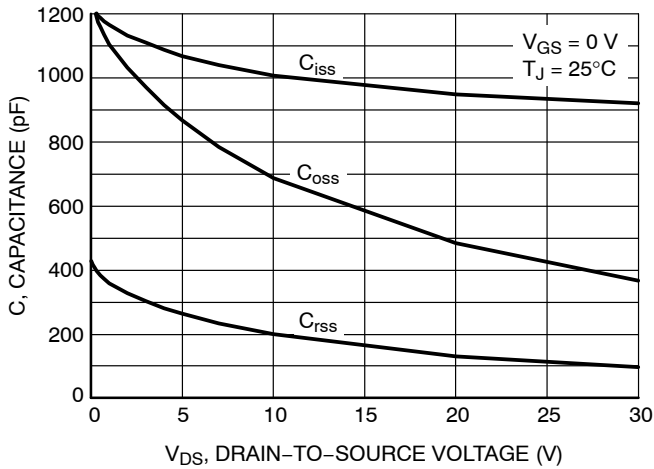


Figure 7. Capacitance Variation

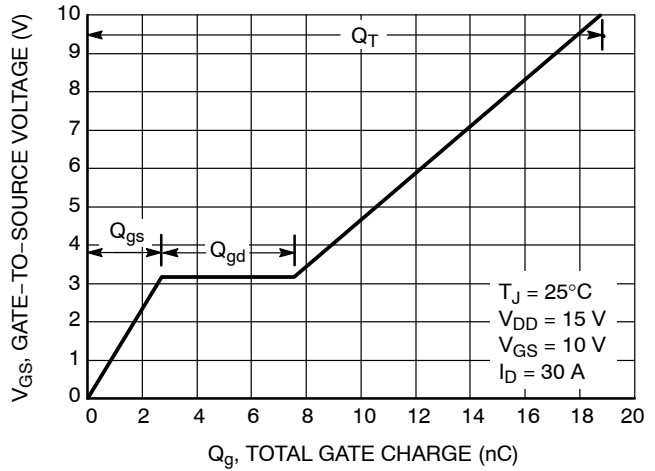


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

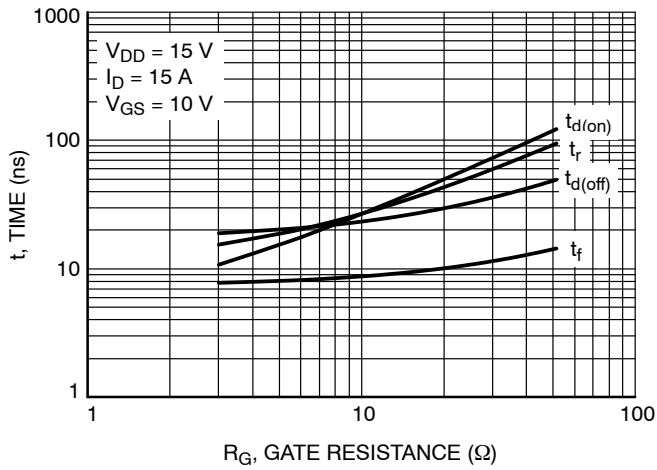


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

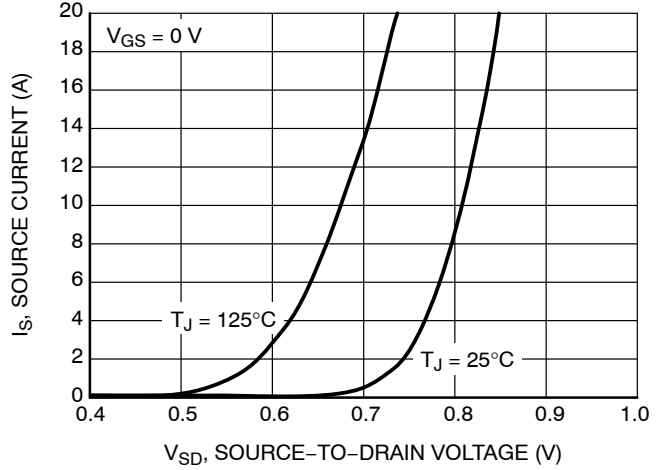


Figure 10. Diode Forward Voltage vs. Current

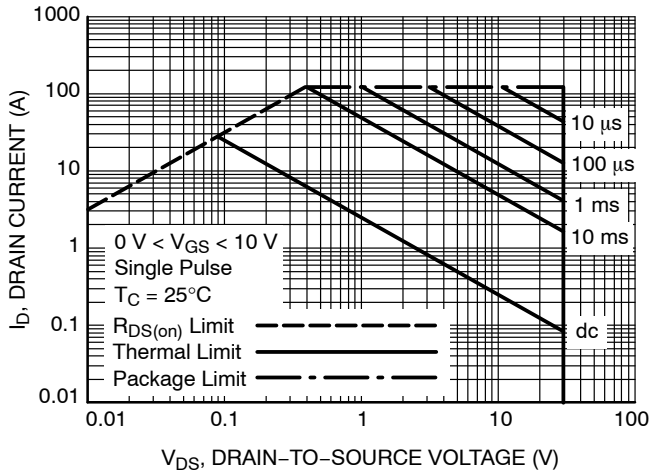


Figure 11. Maximum Rated Forward Biased Safe Operating Area

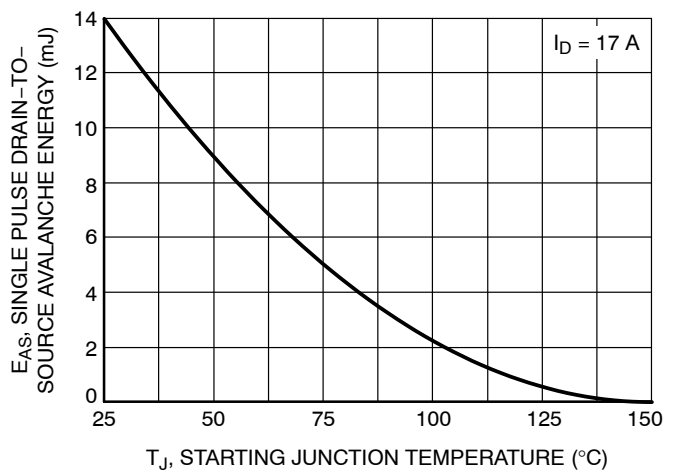


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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## TYPICAL CHARACTERISTICS



Figure 13. Thermal Response

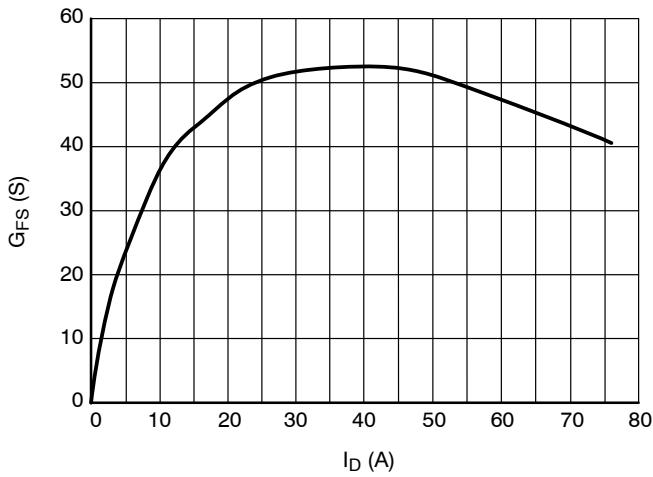


Figure 14.  $G_{FS}$  vs.  $I_D$

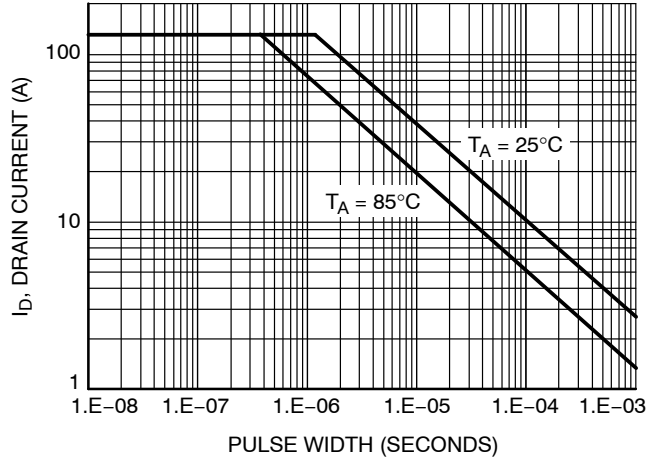


Figure 15. Avalanche Characteristics

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

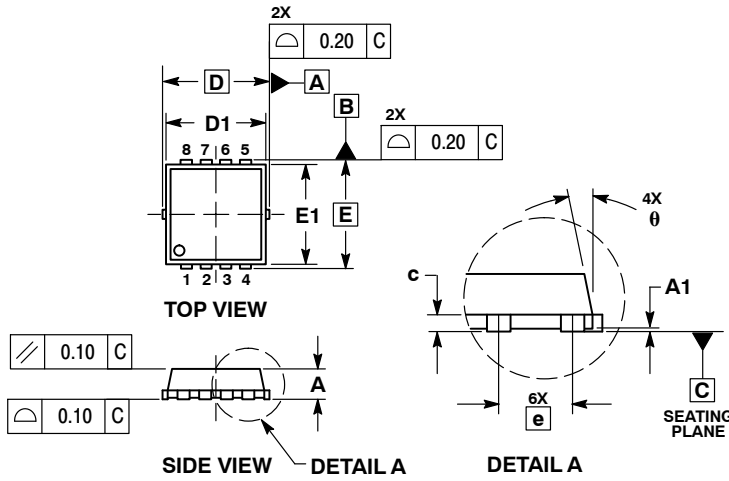
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SCALE 2:1

### WDFN8 3.3x3.3, 0.65P CASE 511AB ISSUE D

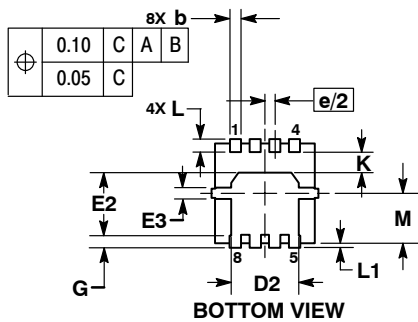
DATE 23 APR 2012



NOTES:

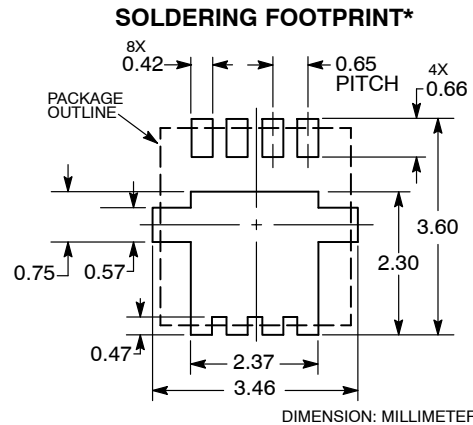
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	---	0.05	0.000	---	0.002
b	0.23	0.30	0.40	0.009	0.012	0.016
c	0.15	0.20	0.25	0.006	0.008	0.010
D	3.30 BSC			0.130 BSC		
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
E	3.30 BSC			0.130 BSC		
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	0.23	0.30	0.40	0.009	0.012	0.016
e	0.65 BSC			0.026 BSC		
G	0.30	0.41	0.51	0.012	0.016	0.020
K	0.65	0.80	0.95	0.026	0.032	0.037
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
M	1.40	1.50	1.60	0.055	0.059	0.063
θ	0°	---	12°	0°	---	12°



- XXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.  
Pb-Free indicator, "G" or microdot "▪", may or may not be present.



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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